



**TO-220BK Plastic-Encapsulate Thyristors**

**CT316B** 3Q TRIACs

**MAIN CHARACTERISTICS**

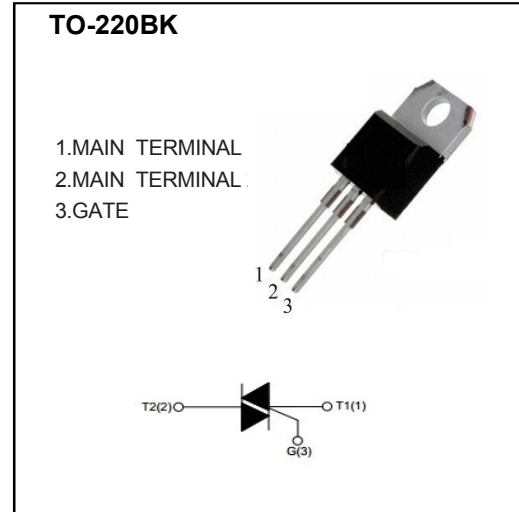
$I_{T(RMS)}$		<b>16A</b>
$V_{DRM}/V_{RRM}$	CT316B-600S/C/B	<b>600V</b>
	CT316B-800S/C/B	<b>800V</b>
$V_{TM}$		<b>1.55V</b>

**FEATURES**

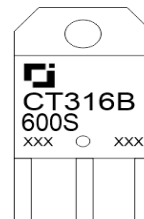
- NPNPN 5-layer Structure TRIACs
- Mesa Glass Passivated Technology
- Multi Layers Metal Electrodes
- High Junction Temperature
- Good Commutation Performance
- High  $dV/dt$  and  $dI/dt$

**APPLICATIONS**

- Heater Control
- Motor Speed Controller
- Mixer



**MARKING**



CT316B:Series Code  
 600S:Depends on  $V_{DRM}$   
 and  $I_{GT}$   
 XXX:Internal Code

**ABSOLUTE RATINGS (  $T_a=25^\circ\text{C}$  unless otherwise noted )**

Symbol	Parameter	Test condition	Value	Unit	
$V_{DRM}/V_{RRM}$	Repetitive peak off-state voltage	$T_j=25^\circ\text{C}$	CT316B-600S/C/B	600	V
			CT316B-800S/C/B	800	V
$I_{T(RMS)}$	RMS on-state current	TO-220BK( $T_c \leq 110^\circ\text{C}$ ), Fig. 1,2	16	A	
$I_{TSM}$	Non repetitive surge peak on-state current	Full sine wave , $T_j(\text{init})=25^\circ\text{C}$ , $t_p=20\text{ms}$ ; Fig. 3,5	160	A	
$I^2t$	$I^2t$ value	$t_p=10\text{ms}$	140	$\text{A}^2\text{s}$	
$dI_T/dt$	Critical rate of rise of on-state current	$I_G=2 \cdot I_{GT}$ , $t_r \leq 10\text{ns}$ , $F=120\text{Hz}$ , $T_j=125^\circ\text{C}$	I - II - III	50	$\text{A}/\mu\text{s}$
			IV	n/a	
$I_{GM}$	Peak gate current	$t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$	4	A	
$P_{G(AV)}$	Average gate power	$T_j=125^\circ\text{C}$	1	W	
$T_{STG}$	Storage temperature		-40~+150	$^\circ\text{C}$	
$T_j$	Operating junction temperature		-40~+125		

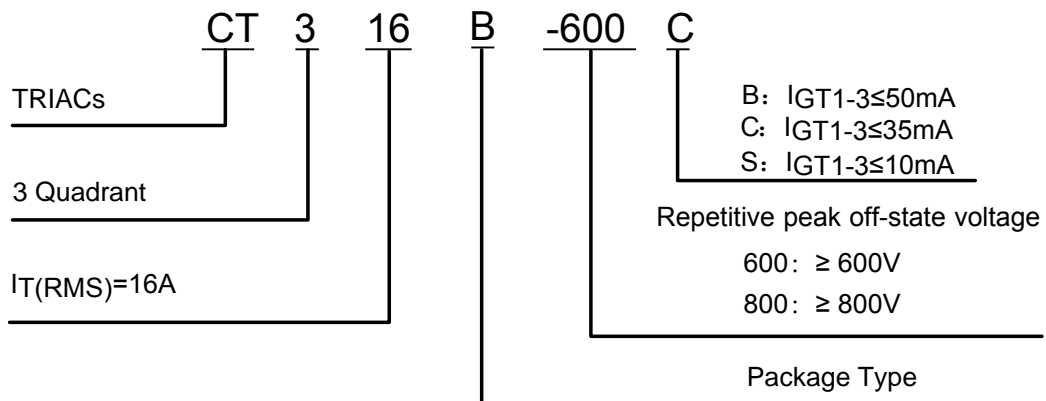
## ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test condition	Value			Unit	
			S	C	B		
I <sub>GT</sub>	Gate trigger current	V <sub>D</sub> =12V, R <sub>L</sub> =33Ω, T <sub>j</sub> =25°C, Fig. 6	I - II -III	≤10	≤35	≤50	mA
			IV	n/a	n/a	n/a	
V <sub>GT</sub>	Gate trigger voltage	T <sub>j</sub> =25°C, Fig. 6	I - II -III	≤1.3			V
V <sub>GD</sub>	Non-triggering gate voltage	V <sub>D</sub> =V <sub>DRM</sub> , T <sub>j</sub> =125°C	≥0.2			V	
I <sub>H</sub>	Holding current	I <sub>T</sub> =500mA, Fig. 6	≤15	≤30	≤50	mA	
I <sub>L</sub>	Latching current	I <sub>G</sub> =1.2I <sub>GT</sub> Fig. 6	I - III	≤25	≤50	≤70	mA
			II	≤30	≤60	≤80	mA
dV <sub>D</sub> /dt	Critical rate of rise of off-state	V <sub>D</sub> =67%V <sub>DRM</sub> , Gate Open T <sub>j</sub> =125°C	≥40	≥500	≥1000	V/μs	
V <sub>TM</sub>	On-state Voltage	I <sub>TM</sub> =23A, tp=380μs, Fig. 4	≤1.55			V	
I <sub>DRM</sub> / I <sub>RPM</sub>	Repetitive peak off-state current	V <sub>D</sub> =V <sub>DRM</sub> /V <sub>RPM</sub> , T <sub>j</sub> =25°C	≤5	≤5	≤5	μA	
		V <sub>D</sub> =V <sub>DRM</sub> /V <sub>RPM</sub> , T <sub>j</sub> =125°C	≤1	≤1	≤1	mA	

## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>th</sub> (j-c)	Junction to case (AC)	TO-220BK	1.2 °C/W
R <sub>th</sub> (j-a)	Junction to ambient	TO-220BK	60 °C/W

## PART NUMBER



# CHARACTERISTICS CURVES

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

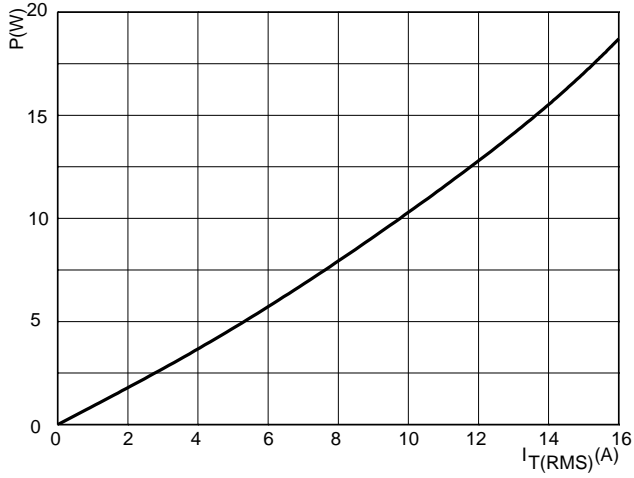


FIG.2: RMS on-state current versus case temperature (full cycle)

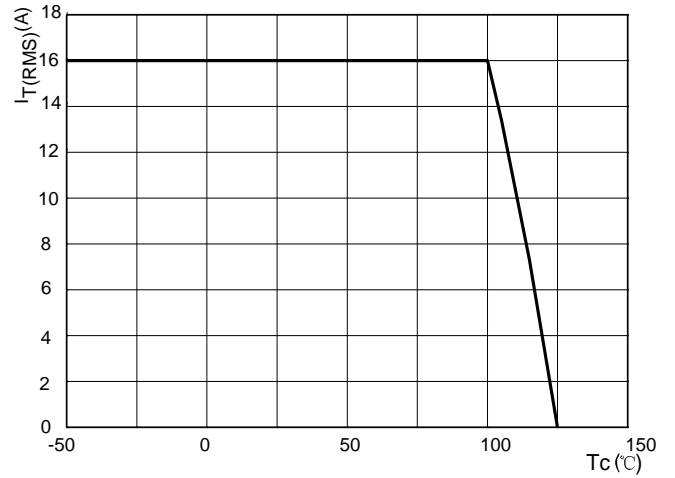


FIG.3: Surge peak on-state current versus number of cycles

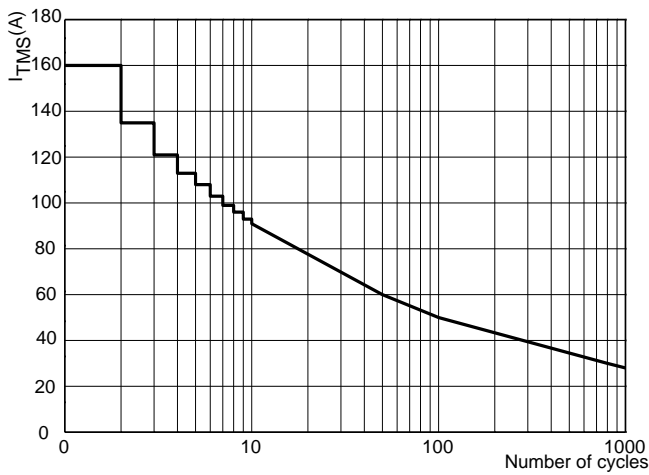


FIG.4: On-state characteristics (maximum values)

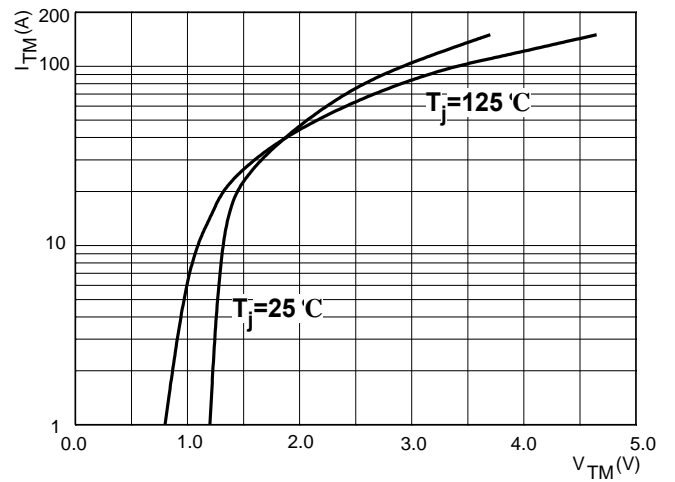


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$

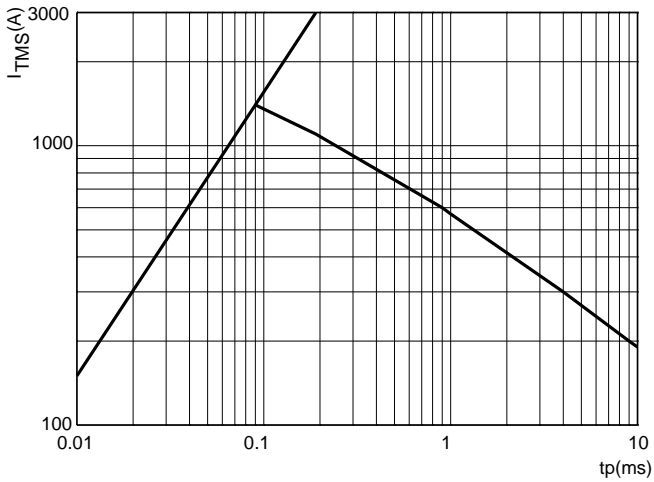
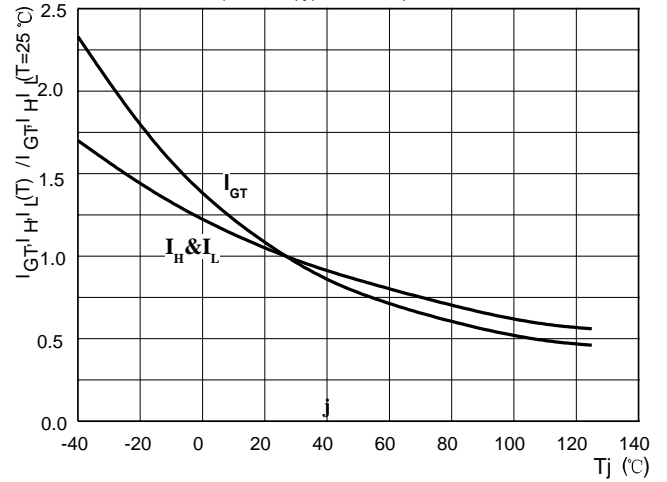
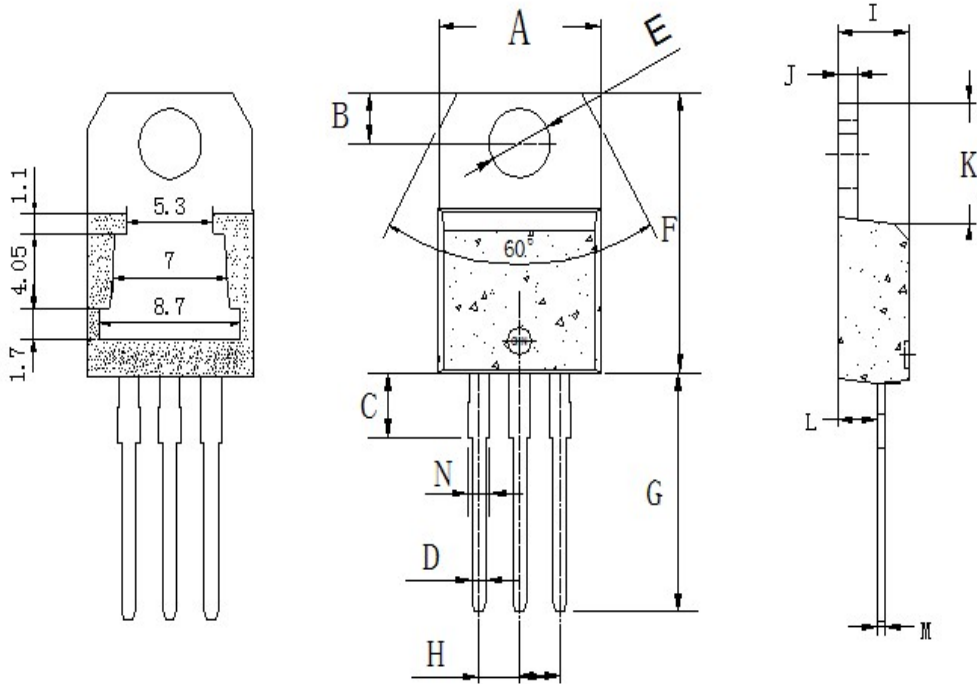


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



# TO-220BK PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	9.8	10.4	0.385	0.409
B	2.65	3.1	0.104	0.122
C	2.8	4.2	0.110	0.165
D	0.7	0.92	0.027	0.036
E	3.75	3.95	0.147	0.155
F	14.8	16.1	0.582	0.633
G	13.05	13.6	0.513	0.535
H	2.4	2.7	0.094	0.106
I	4.38	4.61	0.172	0.181
J	1.15	1.36	0.045	0.053
K	5.85	6.82	0.230	0.268
L	2.35	2.75	0.092	0.108
M	0.35	0.65	0.013	0.025
N	1.18	1.42	0.046	0.055